

IN THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of the Claim:

Please amend the claims as below:

1. (Currently amended) A semiconductor device with ESD protection, comprising:

a guard ring; and

a MOS transistor array formed in a region surrounded by said guard ring and comprising a first MOS transistor and a second MOS transistor, wherein said first MOS transistor is closer to said guard ring than second MOS transistor in a horizontal direction in which ~~said first MOS transistor and said second MOS transistor are arranged alternatively~~ said first MOS transistor is adjacent to said second MOS than said second MOS transistor is;

a first resistor having one end electrically connected to a gate of said first MOS transistor and the other end grounded; and

a second resistor having one end electrically connected to a gate of said second MOS transistor and the other end grounded, wherein a resistance value of said first resistor is greater than that of said second resistor.